

Title (en)

Process for the wet etching of a pyramidal texture on silicium surfaces

Title (de)

Verfahren zum nasschemischen pyramidalen Texturätzen von Siliziumoberflächen

Title (fr)

Procedé pour l'attaque par voie humide de structures pyramidales sur la surface de silicium

Publication

EP 0944114 A3 20000223 (DE)

Application

EP 99104008 A 19990312

Priority

DE 19811878 A 19980318

Abstract (en)

[origin: EP0944114A2] An aqueous alkaline etching solution, for pyramidal texturing of silicon surfaces, contains both isopropanol and an aqueous alkaline ethylene glycol solution. Wet chemical pyramidal texturing of silicon surfaces is carried out using an etching solution which contains water, a basic reagent, isopropanol and an aqueous alkaline ethylene glycol solution. An Independent claim is also included for an etching solution as described above.

IPC 1-7

H01L 21/306

IPC 8 full level

C23F 1/32 (2006.01); **H01L 21/306** (2006.01); **H01L 31/0236** (2006.01)

CPC (source: EP US)

H01L 31/0236 (2013.01 - US); **H01L 31/02363** (2013.01 - EP); **Y02E 10/50** (2013.01 - US)

Citation (search report)

- [A] US 3909325 A 19750930 - CHURCH CLYDE L, et al
- [A] GB 1250653 A 19711020
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- [XA] US 3940356 A 19760224 - BYRNES PETER G

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Designated contracting state (EPC)

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DOCDB simple family (publication)

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EP 99104008 A 19990312; DE 19811878 A 19980318; DE 59914532 T 19990312; ES 99104008 T 19990312; JP 7375999 A 19990318; US 27202299 A 19990318; US 9091502 A 20020305